DATA SHEET
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NPN Silicon Epitaxial Transistor

BCP68T1G

This NPN Silicon Epitaxial Transistor is designed for use in low voltage, high current applications. The device is housed in the SOT−223 package, which is designed for medium power surface mount applications.

Features

- High Current
- The SOT−223 Package Can Be Soldered Using Wave or Reflow
- SOT−223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- The PNP Complement is BCP69T1
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable*
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	20	Vdc
Collector−Base Voltage	V_{CBO}	25	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	1.0	Adc
Collector Current − Peak (Note 2)	I_{CM}	3.0	Adc
Base Current − Continuous	I_B	0.4	Adc
Base Current − Peak	I_{BM}	0.4	Adc
Total Power Dissipation @ T_A = 25°C (Note 1) Derate above 25°C	P_D	 1.5 12	 W mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to 150	°C

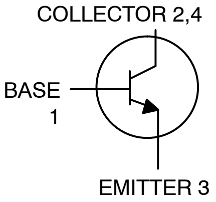
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

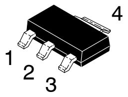
1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.
2. Reference SOA curve for IC peak.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625 in from case Time in Solder Bath	T_L	260 10	°C Sec

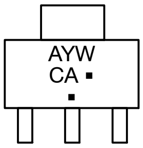
MEDIUM POWER NPN SILICON HIGH CURRENT TRANSISTOR SURFACE MOUNT





SOT−223
CASE 318E
STYLE 1

MARKING DIAGRAM



CA = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping[†]
BCP68T1G	SOT−223 (Pb−Free)	1,000/Tape & Reel
SBCP68T1G*, NSVBCP68T1G*	SOT−223 (Pb−Free)	1,000/Tape & Reel
BCP68T3G	SOT−223 (Pb−Free)	4,000/Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

July, 2024 − Rev. 11

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CES}$	25	–	–	Vdc
Collector−Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	–	–	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector−Base Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)	I_{CBO}	–	–	10	μAdc
Emitter−Base Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	–	–	10	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 5.0 mAdc, V_{CE} = 10 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	h_{FE}	 50 85 60	 – – –	 – 375 –	–
Collector−Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$	–	–	0.5	Vdc
Base−Emitter On Voltage (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	–	–	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	f_T	–	60	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	15	–	pF
Output Capacitance (V_{EB} = 5 Vdc, I_E = 0, f = 1.0 MHz)	C_{ibo}	–	145	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL ELECTRICAL CHARACTERISTICS

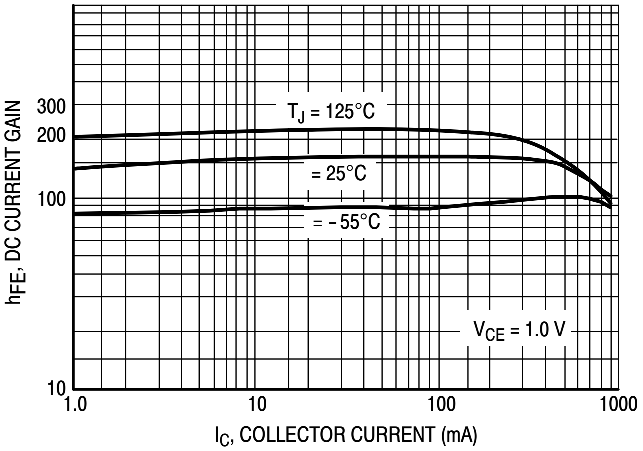


Figure 1. DC Current Gain

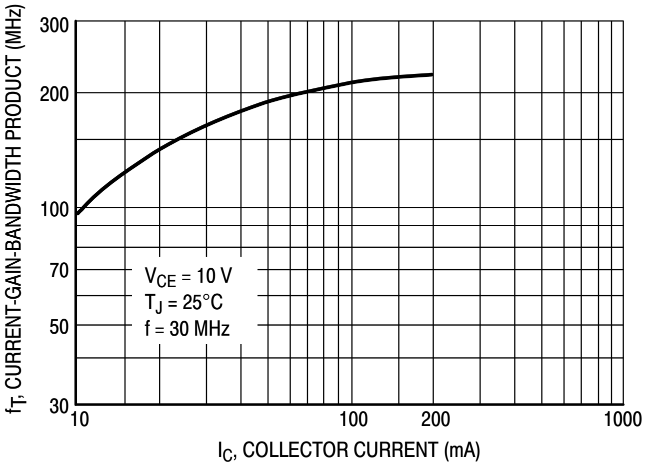


Figure 2. Current-Gain-Bandwidth Product

TYPICAL ELECTRICAL CHARACTERISTICS

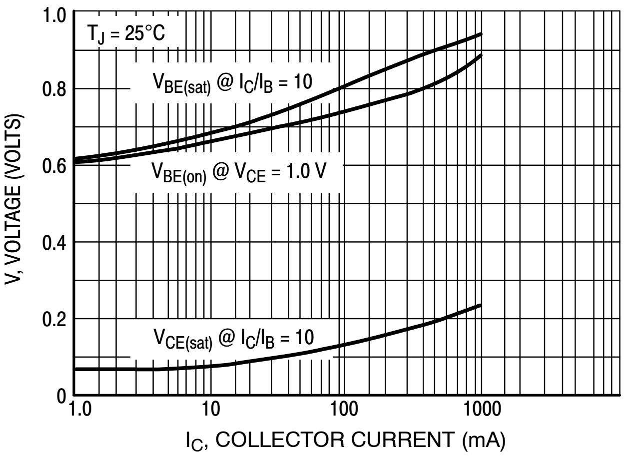


Figure 3. “On” Voltage

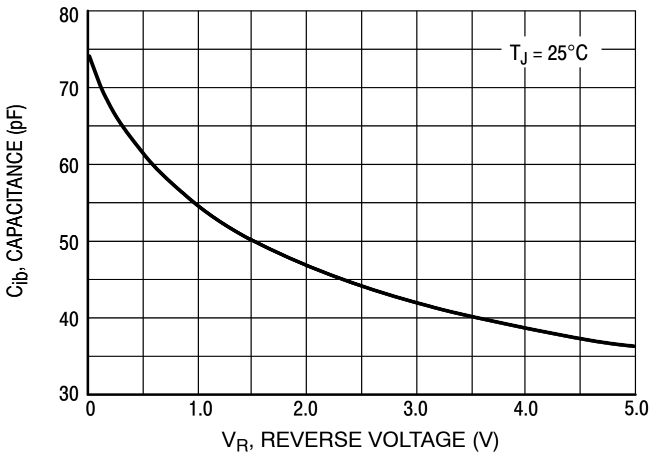


Figure 4. Capacitance

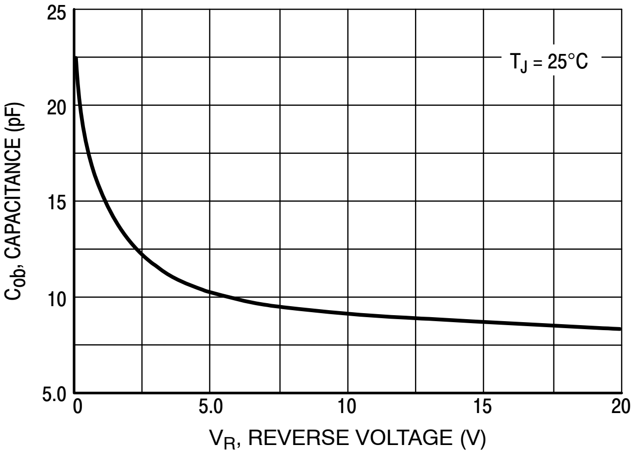


Figure 5. Capacitance

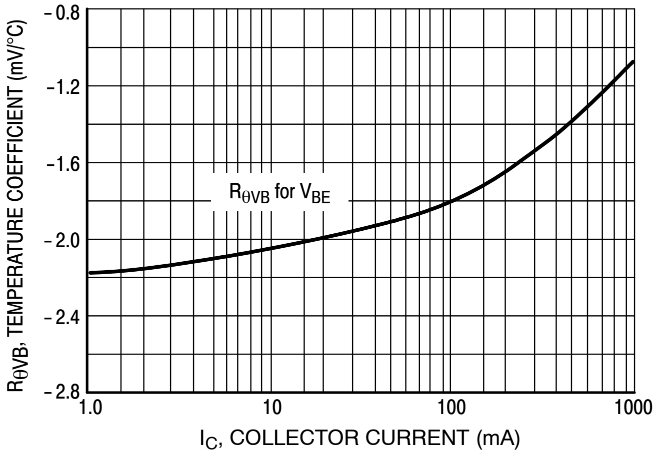


Figure 6. Base−Emitter Temperature Coefficient

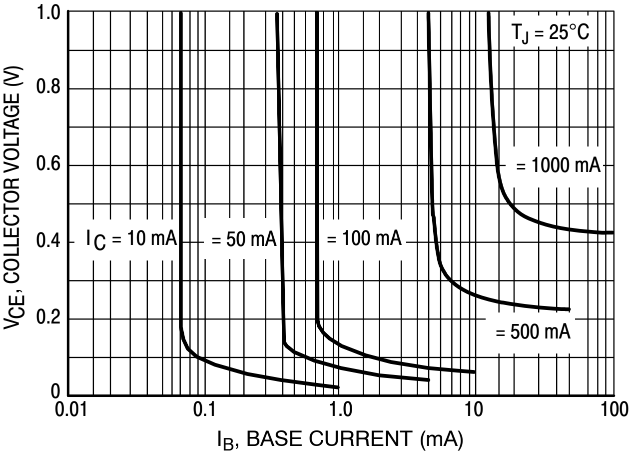


Figure 7. Saturation Region

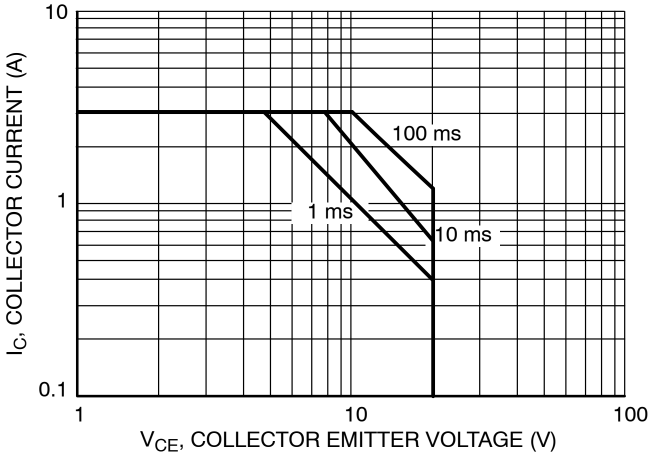


Figure 8. Safe Operating Area

TYPICAL ELECTRICAL CHARACTERISTICS

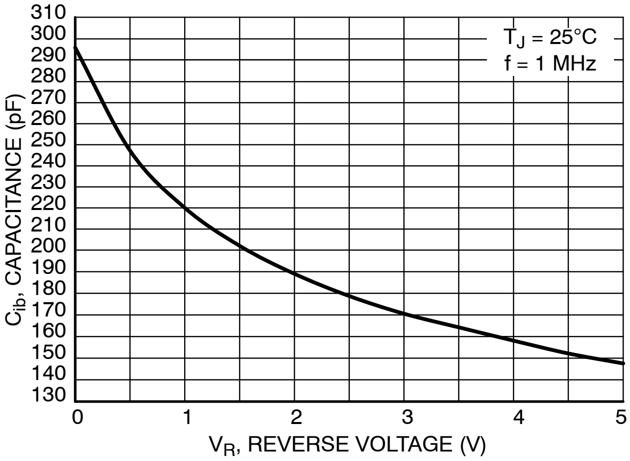


Figure 9. Input Capacitance

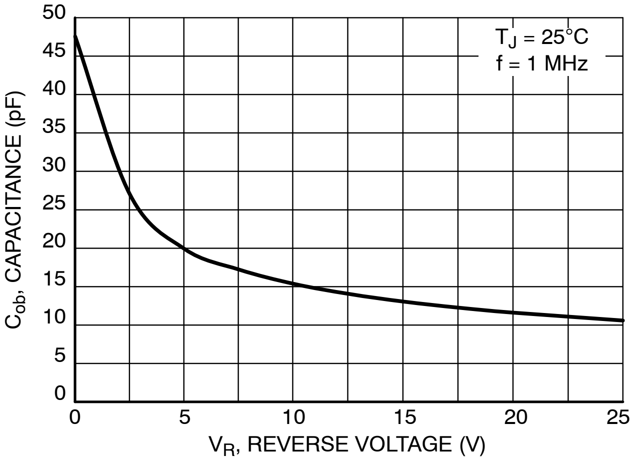


Figure 10. Output Capacitance

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